

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current		20	A
I _{DP}	Pulse Drain Current Tested	T _C =25°C	160	A
		T _C =100°C	100	
I _D ^a	Continuous Drain Current	T _C =25°C	85	A
		T _C =100°C	53	
P _D	Maximum Power Dissipation	T _C =25°C	50	W
		T _C =100°C	20	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	2.5	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient	t ≤ 10s	15	°C/W
		Steady State	50	
I _{AS} ^a	Avalanche Current, Single pulse	L=0.5mH	30	A
E _{AS} ^a	Avalanche Energy, Single pulse	L=0.5mH	225	mJ

Note a : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

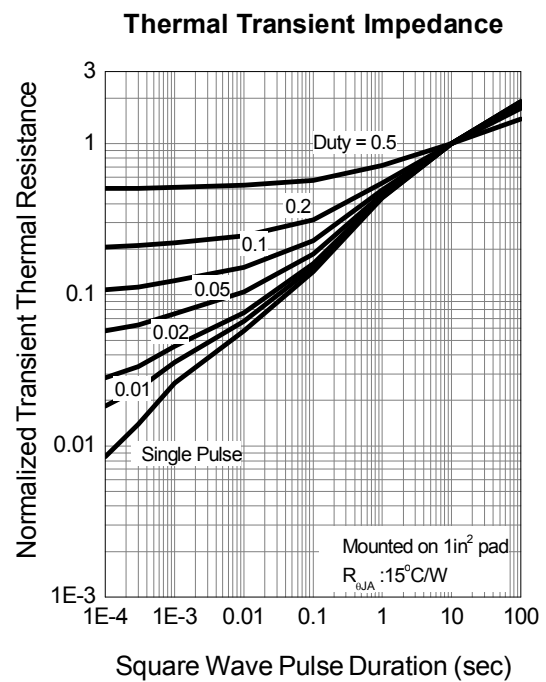
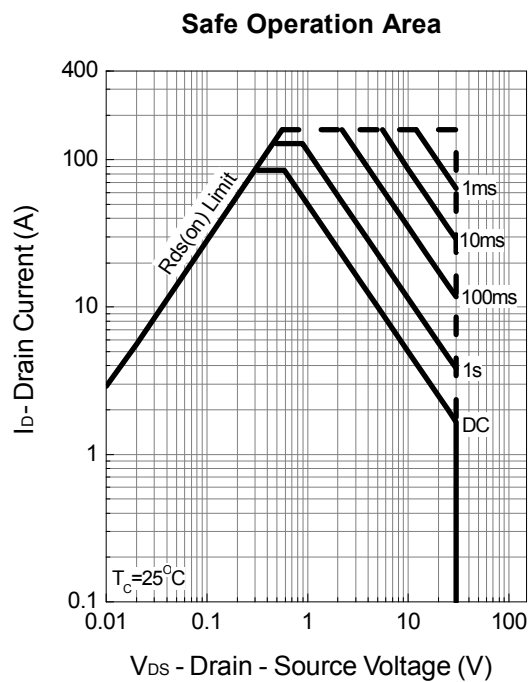
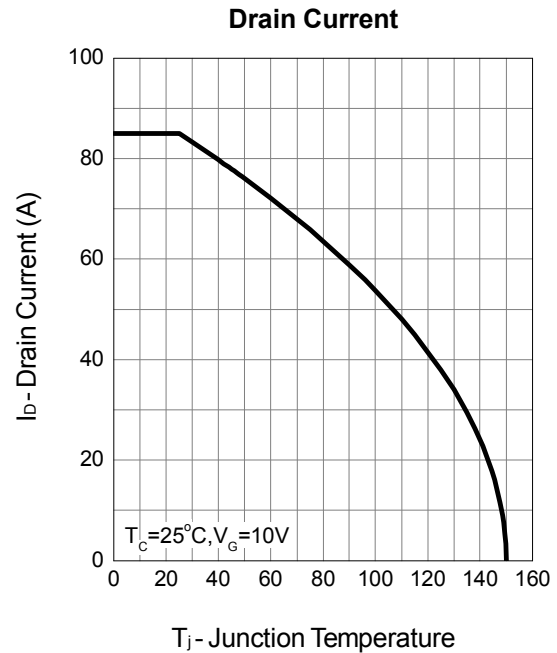
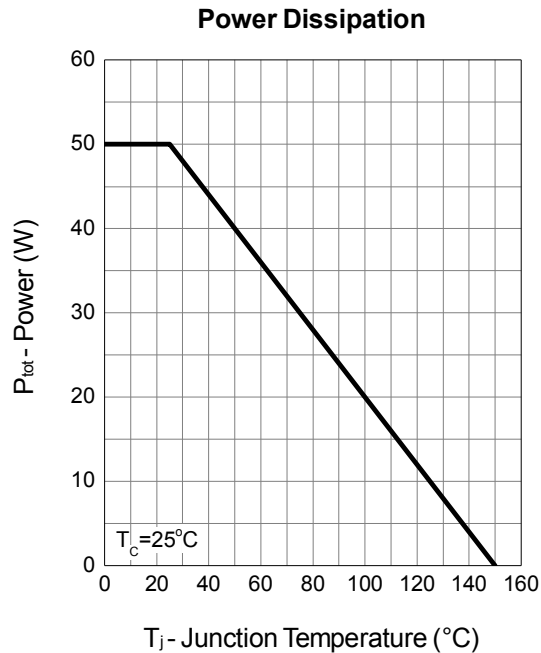
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
BV _{DSS(t)}	Drain-Source Breakdown Voltage (transient)	V _{GS} =0V, I _{D(aval)} =30A T _{case} =25°C, t _{transient} =100ns	34	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.5	1.9	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^b	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =30A	-	2.5	3	mΩ
		T _J =125°C	-	3.8	-	
		V _{GS} =4.5V, I _{DS} =15A	-	3.8	4.6	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =15A	-	50	-	S
Diode Characteristics						
V _{SD} ^b	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.8	1.1	V
t _{rr}	Reverse Recovery Time	I _{DS} =30A, dI _{SD} /dt=100A/μs	-	23	-	ns
t _a	Charge Time		-	13	-	
t _b	Discharge Time		-	11	-	
Q _{rr}	Reverse Recovery Charge		-	9	-	nC
Dynamic Characteristics ^c						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.4	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency= 1.0MHz	-	2450	-	pF
C _{oss}	Output Capacitance		-	590	-	
C _{rss}	Reverse Transfer Capacitance		-	245	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	18	-	ns
t _r	Turn-on Rise Time		-	14	-	
t _{d(OFF)}	Turn-off Delay Time		-	46	-	
t _f	Turn-off Fall Time		-	19	-	
Gate Charge Characteristics ^c						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =30A	-	18	-	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =30A	-	40.3	-	
Q _{gth}	Threshold Gate Charge		-	2.4	-	
Q _{gs}	Gate-Source Charge		-	5	-	
Q _{gd}	Gate-Drain Charge		-	10.5	-	

Note b : Pulse test; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

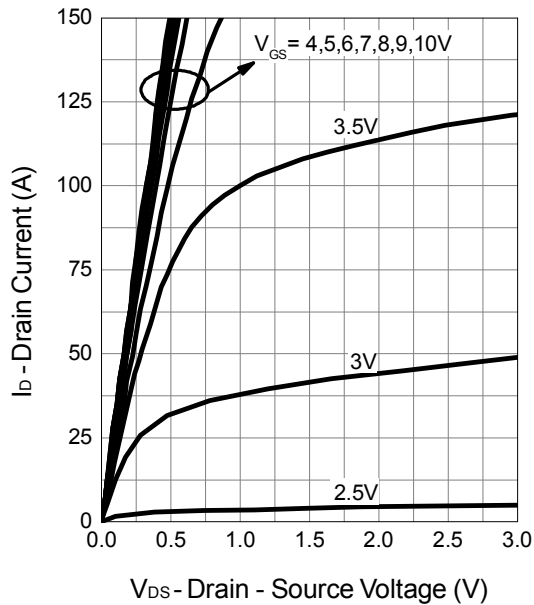
Note c : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

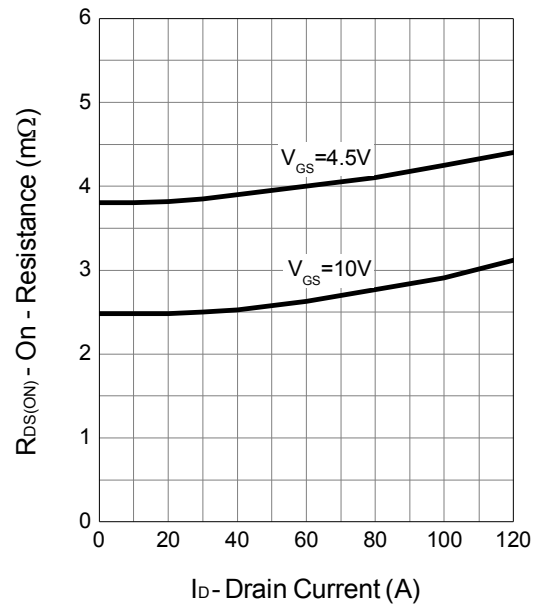


Typical Operating Characteristics (Cont.)

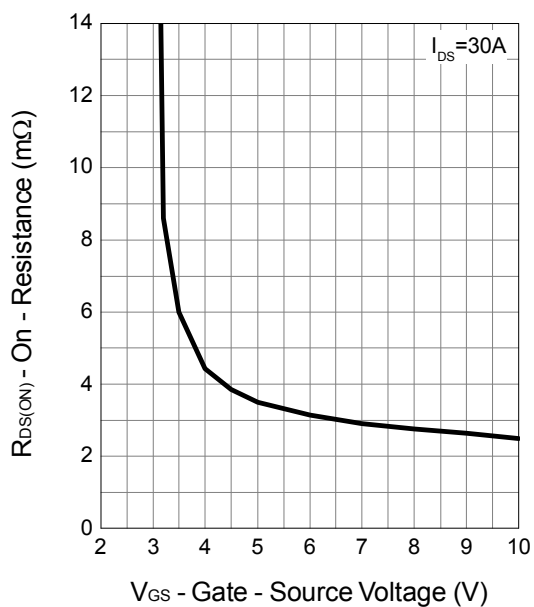
Output Characteristics



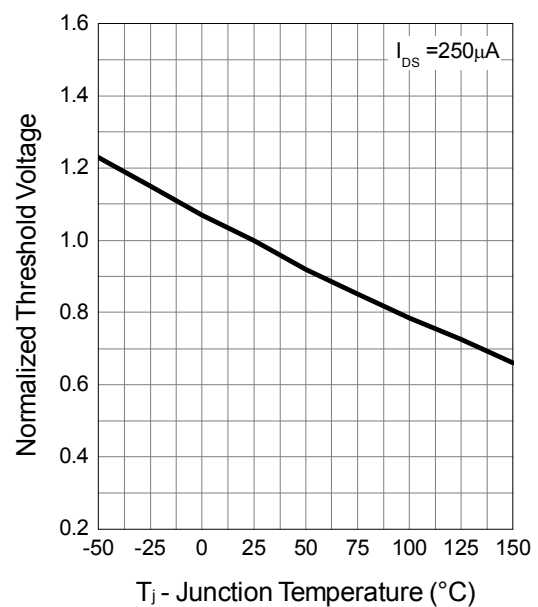
Drain-Source On Resistance



Gate-Source On Resistance

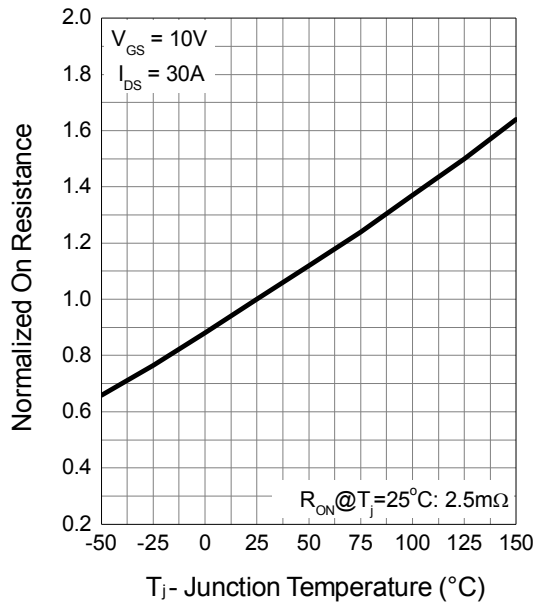


Gate Threshold Voltage

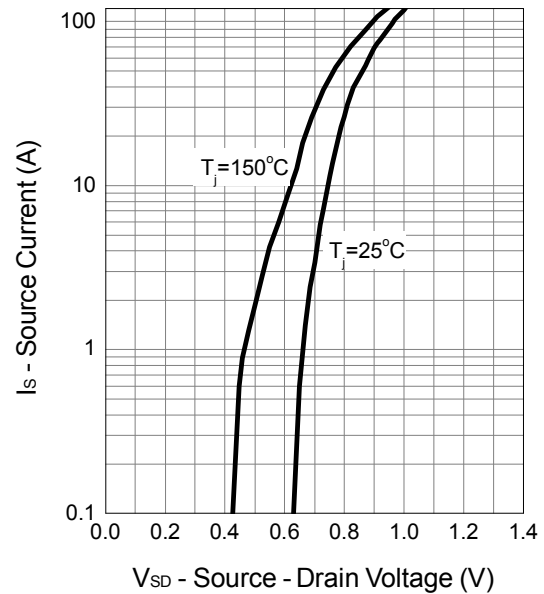


Typical Operating Characteristics (Cont.)

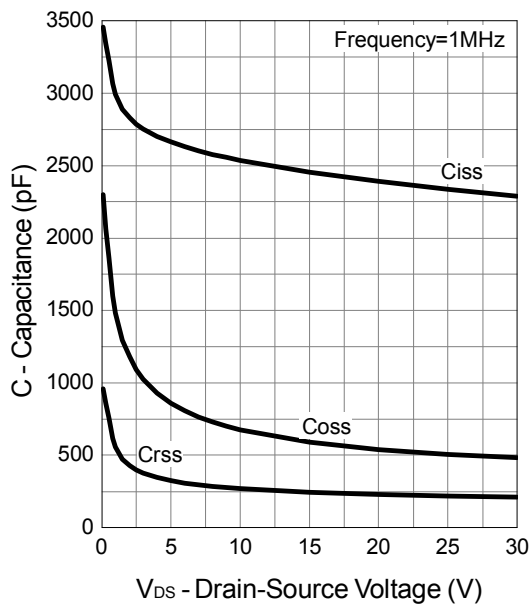
Drain-Source On Resistance



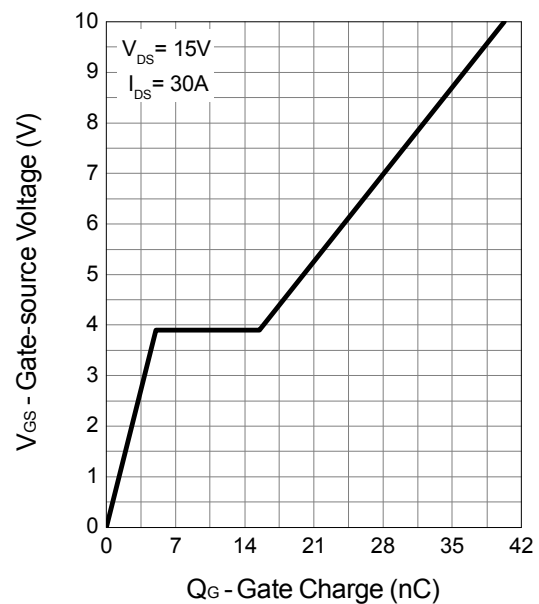
Source-Drain Diode Forward



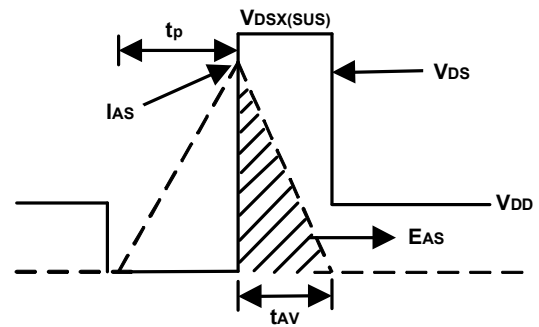
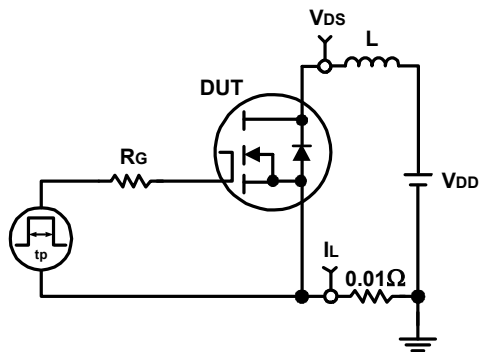
Capacitance



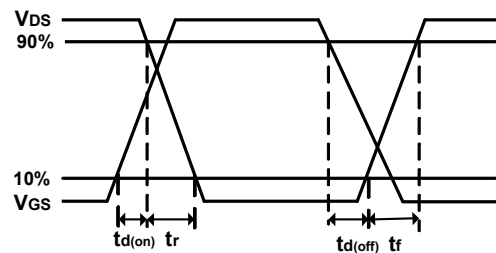
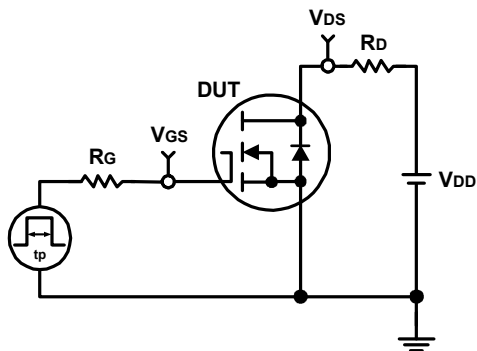
Gate Charge



Avalanche Test Circuit and Waveforms

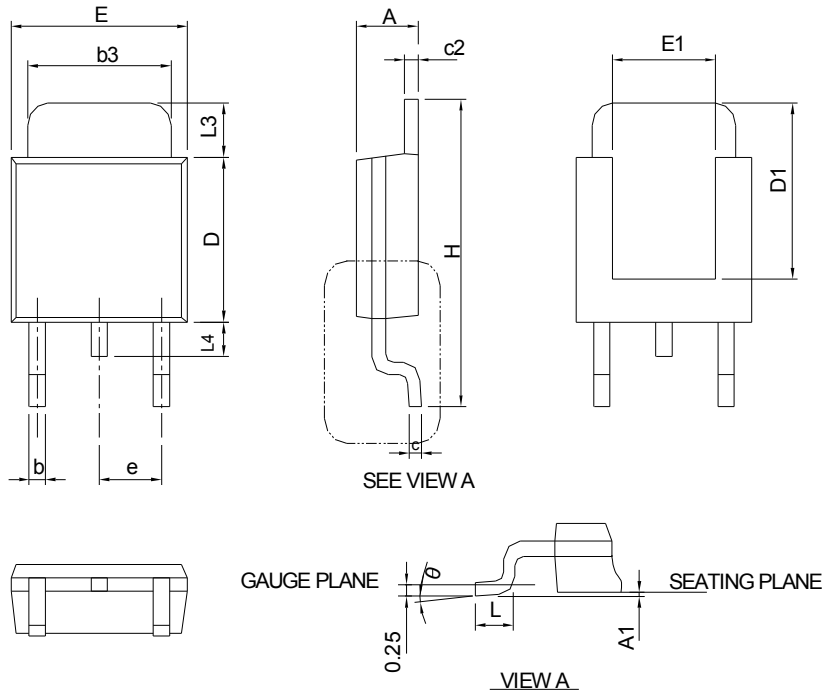


Switching Time Test Circuit and Waveforms



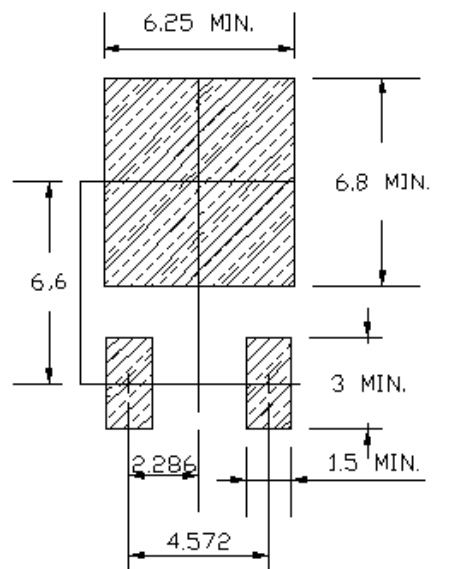
Package Information

TO-252-3



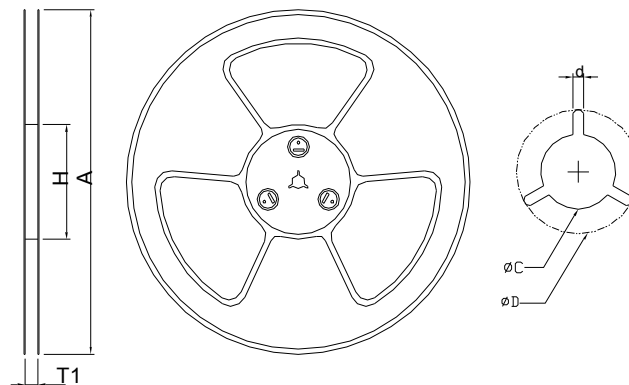
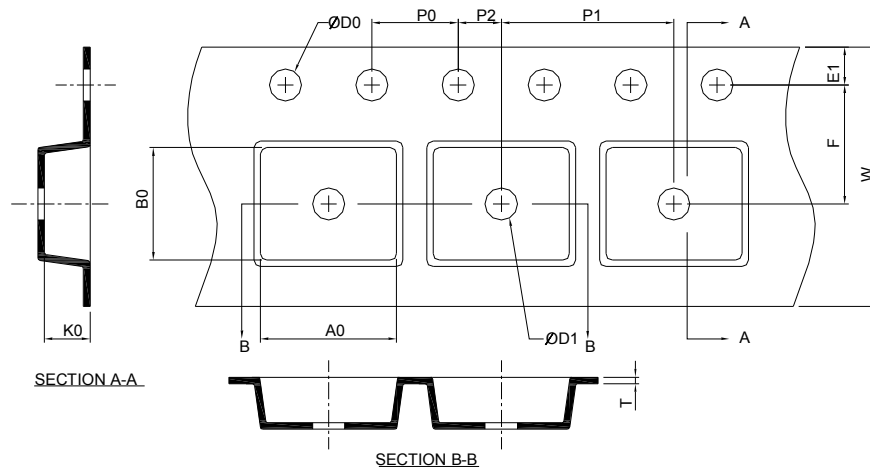
DIMENSIONS	TO-252-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm

Carrier Tape & Reel Dimensions

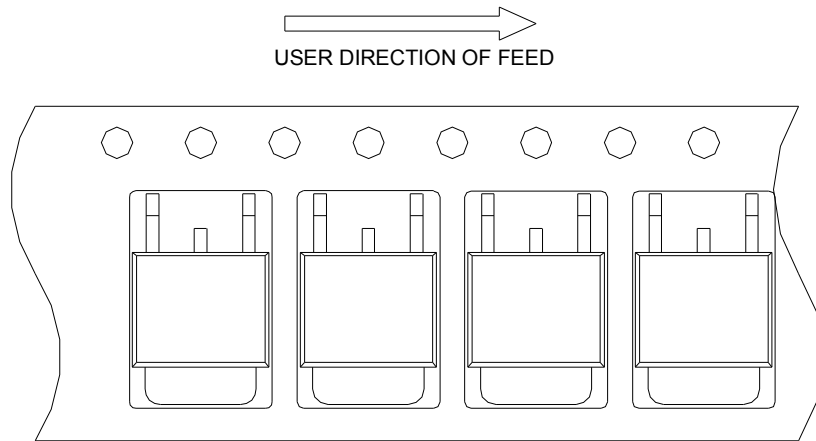


Application	A	H	T1	C	d	D	W	E1	F
TO-252-3	330.0±2.00	50 MIN.	16.4+2.00-0.00	13.0+0.50-0.20	1.5 MIN.	20.2 MIN.	16.0±0.30	1.75±0.10	7.50±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	8.0±0.10	2.0±0.05	1.5+0.10-0.00	1.5 MIN.	0.6+0.00-0.40	6.80±0.20	10.40±0.20	2.50±0.20

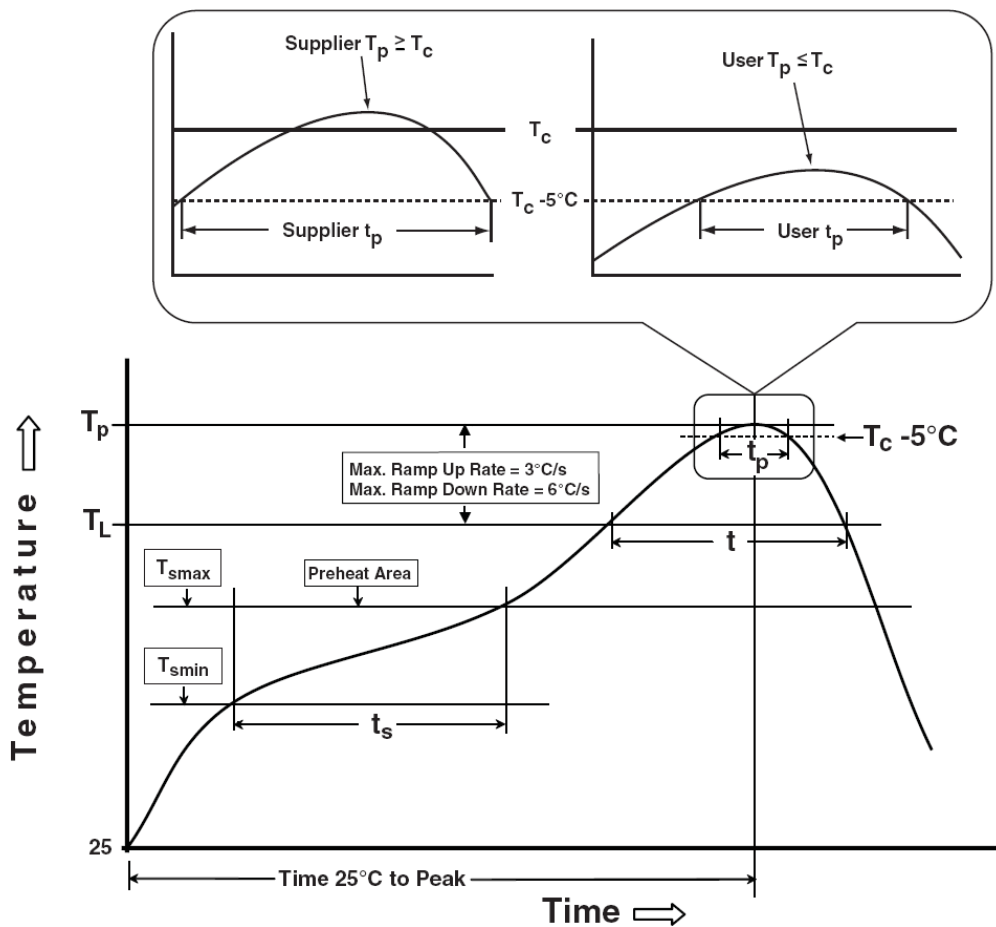
(mm)

Taping Direction Information

TO-252-3



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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